



TFF1012HN

Integrated mixer oscillator PLL for satellite LNB

Rev. 1 — 10 October 2013

Product data sheet

1. General description

The TFF1012HN is an integrated downconverter for use in Low Noise Block (LNB) converters in a 10.7 GHz to 12.75 GHz K_u band satellite receiver system.

2. Features and benefits

- Low current consumption integrated pre-amplifier, mixer, buffer amplifier and PLL synthesizer
- Flat gain over frequency
- Single 5 V supply pin
- Low cost 25 MHz crystal
- Crystal controlled LO frequency generation
- Switched LO frequency (9.75 GHz and 10.6 GHz)
- Low phase noise
- Low spurious
- Low external component count
- Alignment-free concept
- ESD protection on all pins

3. Applications

- K_u band LNB converters for digital satellite reception (DVB-S / DVB-S2)

4. Quick reference data

Table 1. Quick reference data

$V_{CC} = 5\text{ V}$; $T_{amb} = 25\text{ }^\circ\text{C}$; $f_{LO} = 9.75\text{ GHz or }10.6\text{ GHz}$; $f_{xtal} = 25\text{ MHz}$; $Z_0 = 50\text{ }\Omega$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage	RF input and IF output AC coupled	1 4.5	5	5.5	V
I_{CC}	supply current	RF input and IF output AC coupled	1 -	52	-	mA
NF_{SSB}	single sideband noise figure		-	9	-	dB
$f_{i(RF)}$	RF input frequency	low band	10.7	-	11.7	GHz
		high band	11.7	-	12.75	GHz
G_{conv}	conversion gain	measured at low band $f_{IF} = 1450\text{ MHz}$ and high band $f_{IF} = 1625\text{ MHz}$	-	30	-	dB



Table 1. Quick reference data ...continued

$V_{CC} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $f_{LO} = 9.75\text{ GHz}$ or 10.6 GHz ; $f_{xtal} = 25\text{ MHz}$; $Z_0 = 50\text{ }\Omega$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
S_{11}	input reflection coefficient	$f_{i(RF)} = 10.7\text{ GHz}$ to 12.7 GHz	-	-10	-	dB
S_{22}	output reflection coefficient	$f_{o(IF)} = 950\text{ MHz}$ to 2150 MHz ; $Z_0 = 75\text{ }\Omega$	-	-10	-	dB
$IP3_o$	output third-order intercept point	carrier power = -10 dBm (measured at output)	-	17.5	-	dBm

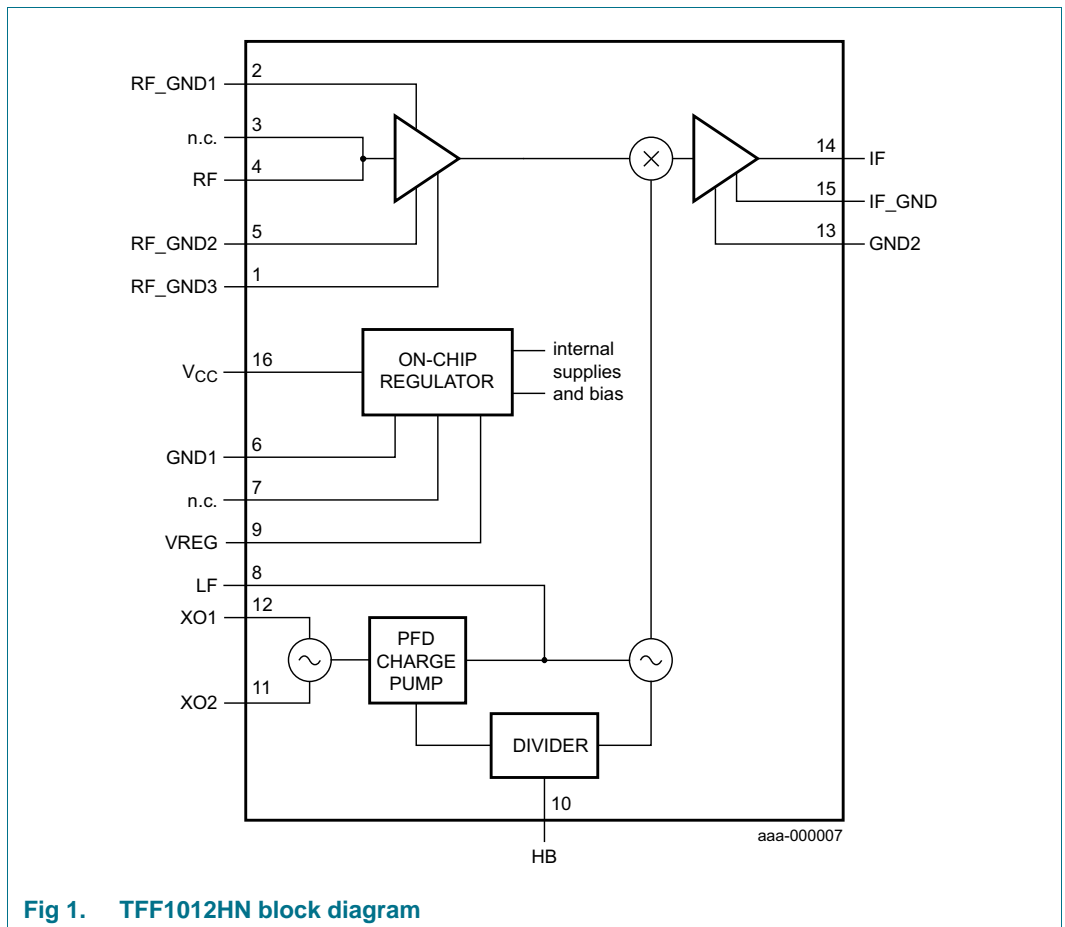
[1] DC values.

5. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
TFF1012HN	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85\text{ mm}$	SOT763-1

6. Block diagram



7. Functional diagram

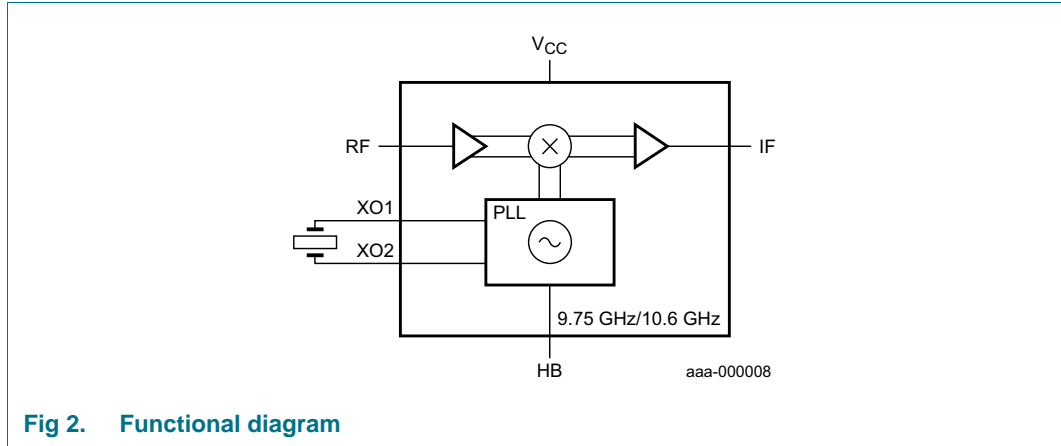


Fig 2. Functional diagram

8. Pinning information

8.1 Pinning

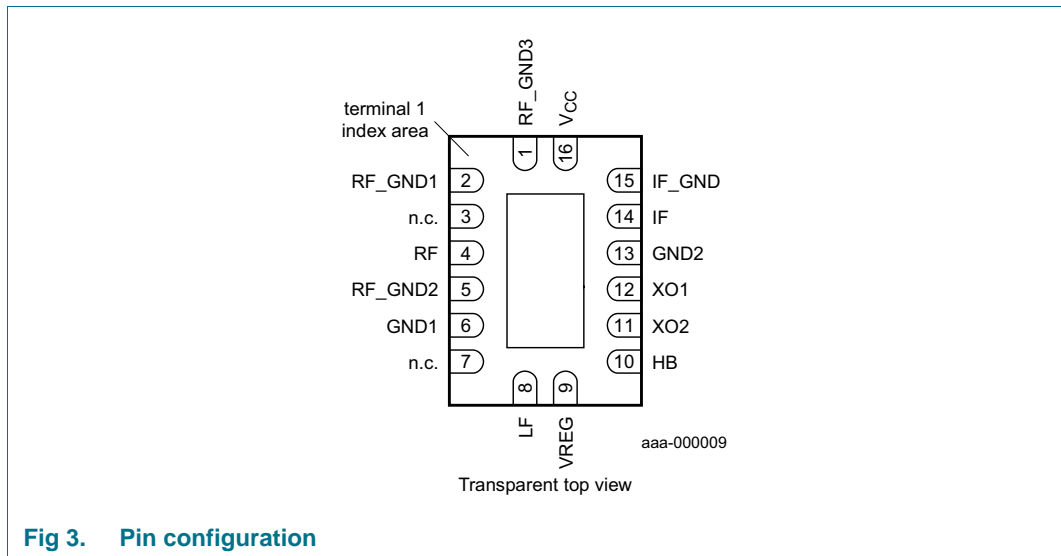


Fig 3. Pin configuration

8.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
GND	0	ground (exposed die pad)
RF_GND3	1	RF ground. Connect this pin to the exposed die pad landing.
RF_GND1	2	RF ground. Connect this pin to the exposed die pad landing and the RF input CPW line.
n.c.	3	not connected. Connect to RF on PCB. [1]
RF	4	RF input.
RF_GND2	5	RF ground. Connect this pin to the exposed die pad landing and the RF input CPW line.

Table 3. Pin description ...continued

Symbol	Pin	Description
GND1	6	Ground. Connect this pin to the exposed die pad landing and the RF input CPW line.
n.c.	7	not connected. Use this pin to route the ground layer on top of the PCB to the exposed die pad.
LF	8	Loop filter PLL. Connect loop filter between this pin and VREG (pin 9).
VREG	9	Regulated output voltage for PLL loop filter. Connect loop filter to this pin. Decouple against die pad via pin 7.
HB	10	High band / low band selection. Connect this pin to the tone detector or to a logic signal.
XO2	11	Crystal connection 2. Connect crystal between this pin and XO1 (pin 12).
XO1	12	Crystal connection 1. Connect crystal between this pin and XO2 (pin 11).
GND2	13	Ground. Connect this pin to the exposed die pad landing.
IF	14	IF output
IF_GND	15	IF output ground. Connect this pin to the exposed die pad landing and the output transmission line ground.
V _{CC}	16	Supply voltage

[1] The distance between the outer edges of pin 2 and 3 is 740 μm . This gives an optimum transition from a 1.1 mm wide, $Z_0 = 50 \Omega$ line on RO4223 Printed-Circuit Board (PCB) material of 0.5 mm height to the TFF1012HN.

9. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6	V
V _{I(HB)}	input voltage on pin HB		-0.5	+6	V
T _{stg}	storage temperature		-40	+125	°C

10. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		4.5	5	5.5	V
V _{I(HB)}	input voltage on pin HB		0	-	5.5	V
T _{amb}	ambient temperature		-40	+25	+85	°C
Z ₀	characteristic impedance		-	50	-	Ω
f _{i(RF)}	RF input frequency	low band	10.7	-	11.7	GHz
		high band	11.7	-	12.75	GHz
f _{LO}	LO frequency	low band	-	9.75	-	GHz
		high band	[1]	10.6	-	GHz
f _{o(IF)}	IF output frequency	low band	0.95	-	1.95	GHz
		high band	1.1	-	2.15	GHz
C _{L(xtal)}	crystal load capacitance		-	10	-	pF
ESR	equivalent series resistance		-	-	40	Ω
f _{xtal}	crystal frequency		-	25	-	MHz

[1] For a 10.75 GHz LO frequency, select high band and use a crystal with frequency $10.75 \text{ GHz} / 424 = 25.353774 \text{ MHz}$.

11. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case		35	K/W

12. Characteristics

Table 7. Characteristics

$V_{CC} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; $f_{LO} = 9.75\text{ GHz}$ or 10.6 GHz ; $f_{xtal} = 25\text{ MHz}$; $Z_0 = 50\ \Omega$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	RF input and IF output AC coupled	[1]	52	-	mA
$\Phi_{n\lambda}(itg)$	integrated phase noise density	integration offset frequency = 10 kHz to 13 MHz; loop bandwidth = crossover bandwidth	-	1.4	-	°RMS
NF_{SSB}	single sideband noise figure	measured at low band $f_{IF} = 1450\text{ MHz}$ and high band $f_{IF} = 1625\text{ MHz}$	-	9	-	dB
G_{conv}	conversion gain	measured at low band $f_{IF} = 1450\text{ MHz}$ and high band $f_{IF} = 1625\text{ MHz}$	-	30	-	dB
ΔG_{conv}	conversion gain variation	over whole IF band in every 36 MHz band	-	2.0	-	dB
S_{11}	input reflection coefficient	$f_{i(RF)} = 10.7\text{ GHz}$ to 12.7 GHz	-	-10	-	dB
S_{22}	output reflection coefficient	$f_{o(IF)} = 950\text{ MHz}$ to 2150 MHz ; $Z_0 = 75\ \Omega$	-	-10	-	dB
$IP3_o$	output third-order intercept point	carrier power is -10 dBm (measured at the output)	-	17.5	-	dBm
$P_{L(1dB)}$	output power at 1 dB gain compression		-	6	-	dBm
$V_{IL(HB)}$	LOW-level input voltage on pin HB		-	-	0.8	V
$V_{IH(HB)}$	HIGH-level input voltage on pin HB		2.0	-	-	V
$R_{pd(HB)}$	pull-down resistance on pin HB		80	110	140	k Ω

[1] DC values.

13. Application information

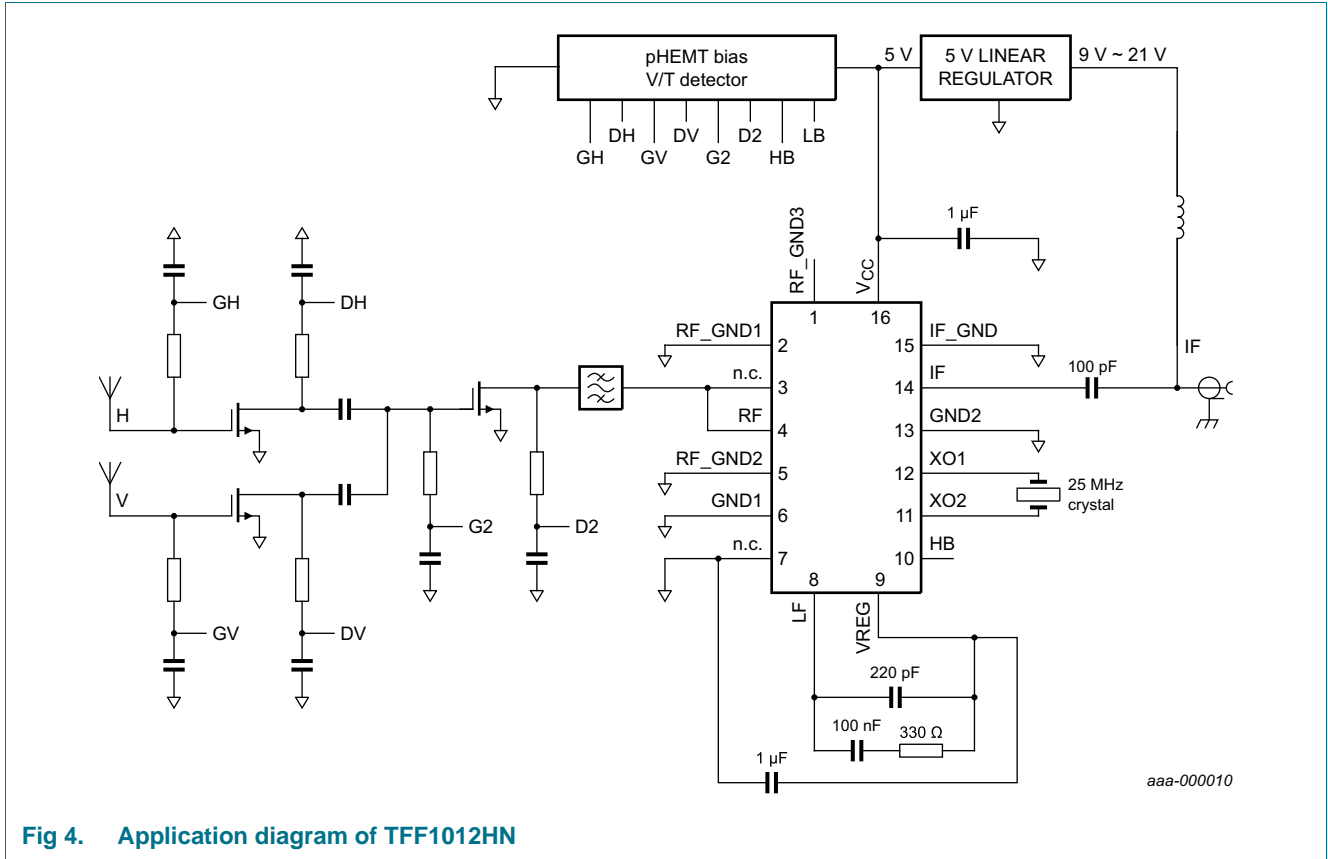


Fig 4. Application diagram of TFF1012HN

Table 8. List of netnames

See [Figure 4](#).

Netname	Description
GH	Gate voltage of 1st stage LNA. Horizontal polarization
DH	Drain voltage of 1st stage LNA. Horizontal polarization
GV	Gate voltage of 1st stage LNA. Vertical polarization
DV	Drain voltage of 1st stage LNA. Vertical polarization
G2	Gate voltage of 2nd stage LNA
D2	Drain voltage of 2nd stage LNA
HB	High band oscillator supply control
LB	Low band oscillator supply control

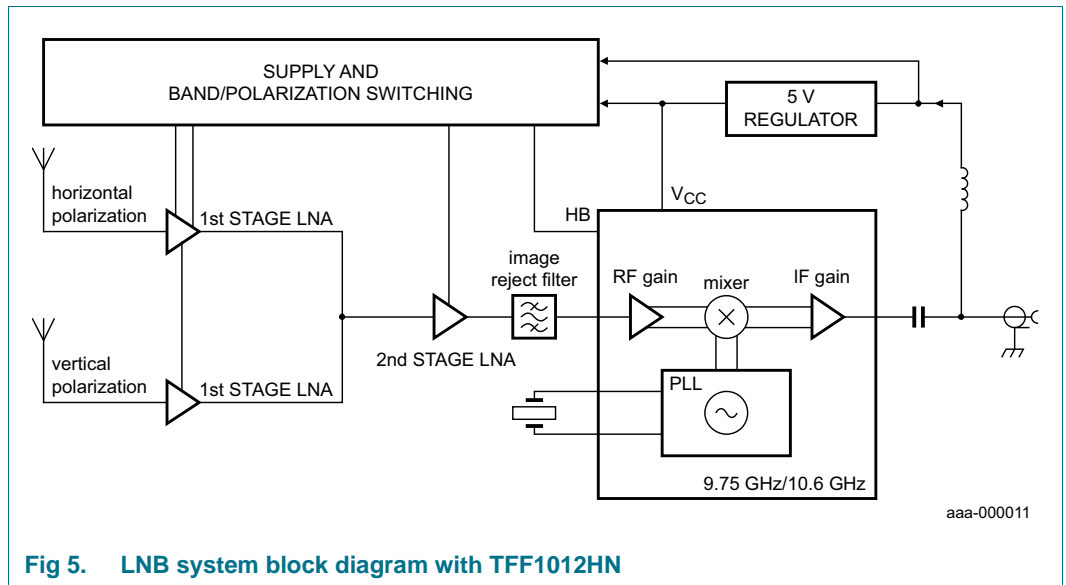


Fig 5. LNB system block diagram with TFF1012HN

14. Package outline

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

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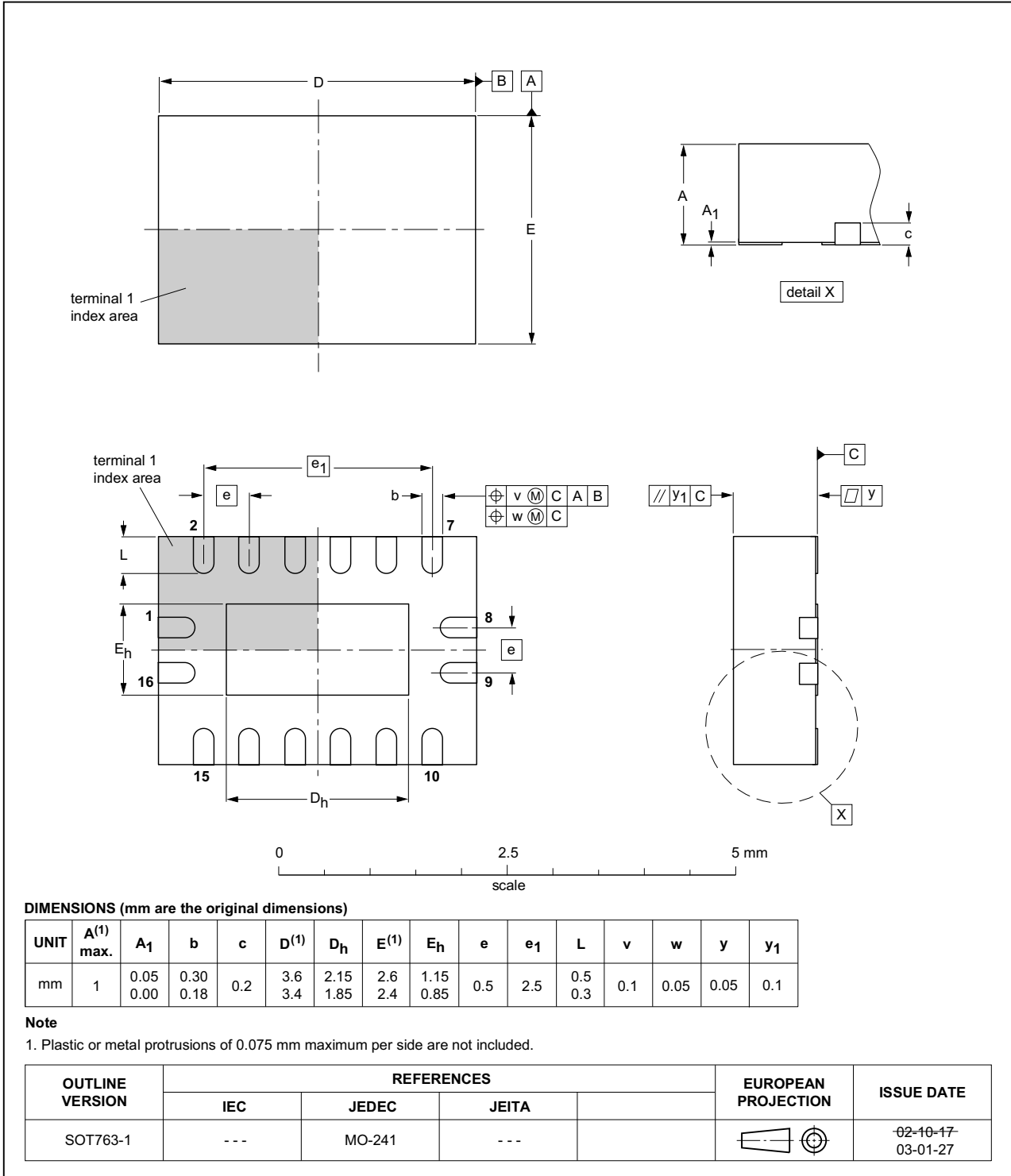


Fig 6. Package outline SOT763-1

15. Abbreviations

Table 9. Abbreviations

Acronym	Description
CPW	CoPlanar Waveguide
DVB-S	Digital Video Broadcasting by Satellite
DVB-S2	Digital Video Broadcasting - Satellite - Second generation
ESD	ElectroStatic Discharge
IF	Intermediate Frequency
K _u band	K-under band
LO	Local Oscillator
PFD	Phase Frequency Detector
pHEMT	Pseudomorphic High Electron Mobility Transistor
PLL	Phase-Locked Loop
V/T	Voltage / Tone
XO	Crystal Oscillator

16. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TFF1012HN v.1	20131010	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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19. Contents

1 **General description** 1

2 **Features and benefits** 1

3 **Applications** 1

4 **Quick reference data** 1

5 **Ordering information** 2

6 **Block diagram** 2

7 **Functional diagram** 3

8 **Pinning information** 3

8.1 Pinning 3

8.2 Pin description 3

9 **Limiting values** 4

10 **Recommended operating conditions** 4

11 **Thermal characteristics** 5

12 **Characteristics** 5

13 **Application information** 6

14 **Package outline** 8

15 **Abbreviations** 9

16 **Revision history** 9

17 **Legal information** 10

17.1 Data sheet status 10

17.2 Definitions 10

17.3 Disclaimers 10

17.4 Trademarks 11

18 **Contact information** 11

19 **Contents** 12

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